

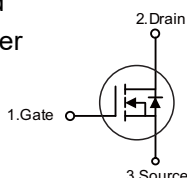
FEATURES

100% EAS Guaranteed
Green Device Available
Super Low Gate Charge
Excellent CdV/dt effect decline
Advanced high cell density Trench technology

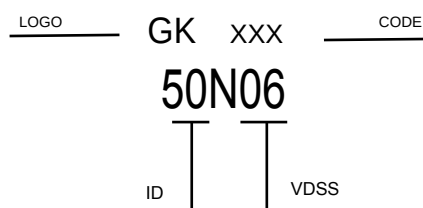
DESCRIPTION

The 50N06 is the high cell density trench N-ch MOSFETs, which provide excellent RDSON and gate charge for most of the synchronous buck converter applications.

The 50N06 meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.



V_{DS} 60 V
 I_D 50 A
 $R_{DS(ON)}$ 11m Ω



MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Absolute Maximum Ratings ($T_C=25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter		Max.	Units
V_{DS}	Drain-Source Voltage		60	V
V_{GS}	Gate-Source Voltage		± 20	V
I_D	Continuous Drain Current	$T_C = 25^\circ\text{C}$	50	A
		$T_C = 100^\circ\text{C}$	29	A
I_{DM}	Pulsed Drain Current ^{note1}		180	A
E_{AS}	Single Pulsed Avalanche Energy ^{note2}		36	mJ
P_D	Power Dissipation	$T_C = 25^\circ\text{C}$	60	W
$R_{\theta JC}$	Thermal Resistance, Junction to Case		2.5	$^\circ\text{C/W}$
T_J, T_{STG}	Operating and Storage Temperature Range		-55 to +150	$^\circ\text{C}$

Electrical characteristics ($T_J=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
Off Characteristic						
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250μA	60	-	-	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =60V, V _{GS} =0V,	-	-	1.0	μA
I _{GSS}	Gate to Body Leakage Current	V _{DS} =0V, V _{GS} = ±20V	-	-	±100	nA
On Characteristics						
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250μA	1.0	1.6	2.5	V
R _{DS(on)}	Static Drain-Source on-Resistance note3	V _{GS} =10V, I _D =20A	-	11	17	mΩ
		V _{GS} =4.5V, I _D =10A	-	14	25	
Dynamic Characteristics						
C _{iss}	Input Capacitance	V _{DS} =25V, V _{GS} =0V, f=1.0MHz	-	2550	-	pF
C _{oss}	Output Capacitance		-	130	-	pF
C _{rss}	Reverse Transfer Capacitance		-	90	-	pF
Q _g	Total Gate Charge	V _{DS} =30V, I _D =20A, V _{GS} =10V	-	22	-	nC
Q _{gs}	Gate-Source Charge		-	4.5	-	nC
Q _{gd}	Gate-Drain(“Miller”) Charge		-	3.5	-	nC
Switching Characteristics						
t _{d(on)}	Turn-on Delay Time	V _{DD} =30V, I _D =20A, R _G =1.6Ω, V _{GS} =10V	-	4.5	-	ns
t _r	Turn-on Rise Time		-	2.7	-	ns
t _{d(off)}	Turn-off Delay Time		-	13.8	-	ns
t _f	Turn-off Fall Time		-	2.7	-	ns
Drain-Source Diode Characteristics and Maximum Ratings						
I _S	Maximum Continuous Drain to Source Diode Forward Current		-	-	45	A
I _{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	180	A
V _{SD}	Drain to Source Diode Forward Voltage	V _{GS} =0V, I _S =30A	-	-	1.2	V
t _{rr}	Body Diode Reverse Recovery Time	T _J =25℃, I _F =20A, dI/dt=100A/μs	-	18	-	ns
Q _{rr}	Body Diode Reverse Recovery Charge		-	12	-	nC

- Notes: 1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature
 2. EAS condition: $T_J=25^\circ\text{C}$, $V_{DD}=30V$, $V_G=10V$, $R_G=25\Omega$, $L=0.5mH$, $I_{AS}=12A$
 3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 0.5\%$

RATING AND CHARACTERISTIC CURVES

Figure1: Output Characteristics

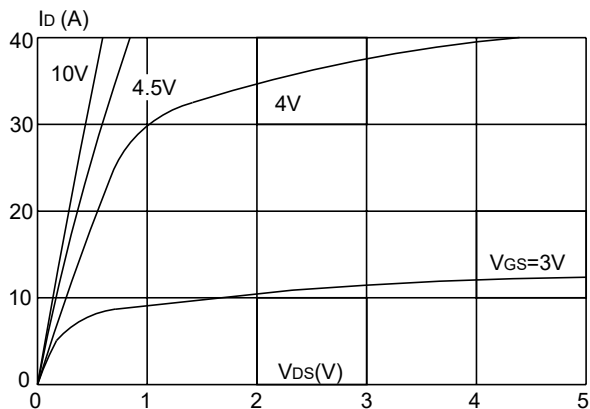


Figure 2: Typical Transfer Characteristics

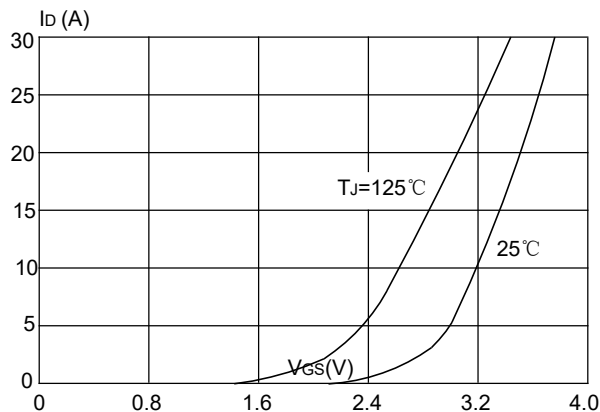


Figure 3: On-resistance vs. Drain Current

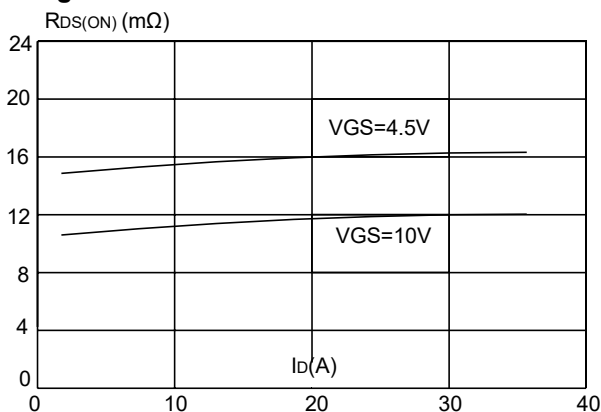


Figure 4: Body Diode Characteristics

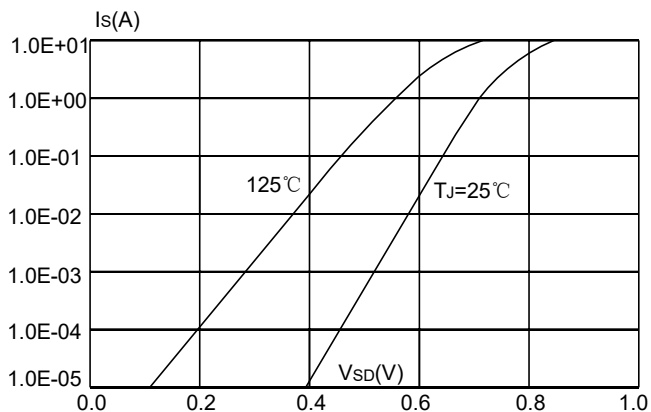


Figure 5: Gate Charge Characteristics

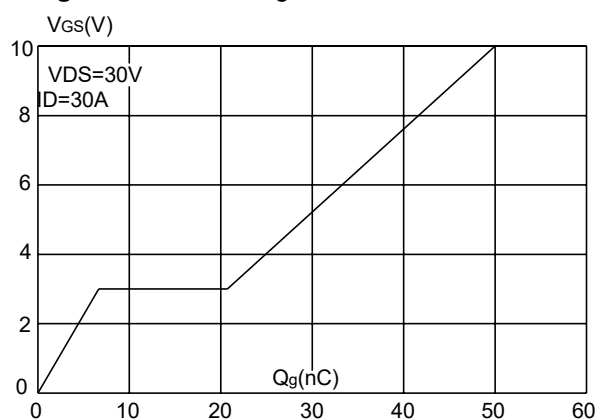
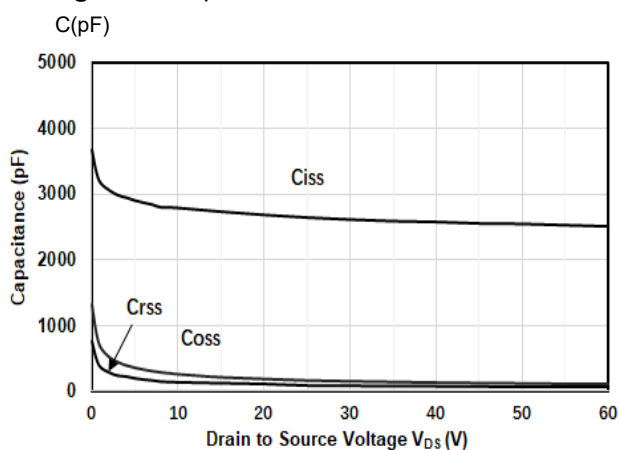


Figure 6: Capacitance Characteristics



RATING AND CHARACTERISTIC CURVES

Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

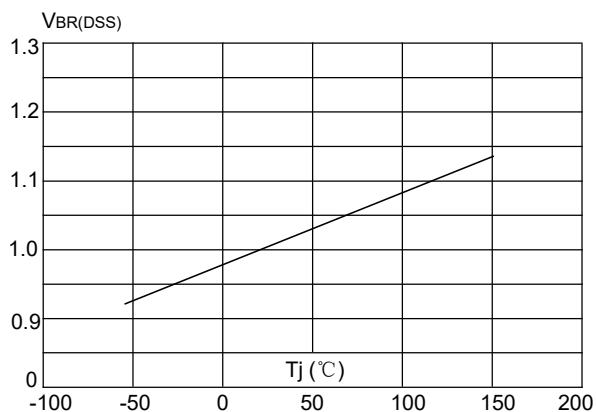


Figure 8: Normalized on Resistance vs. Junction Temperature

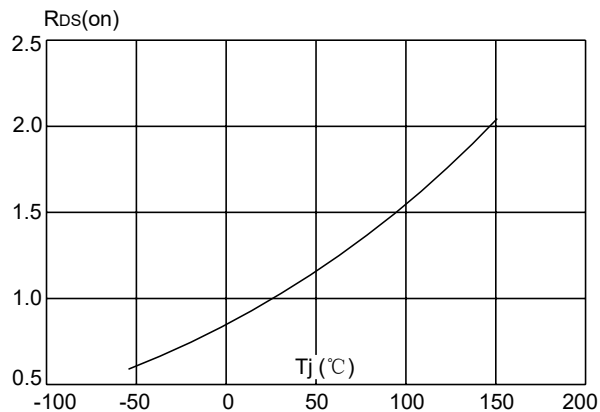


Figure 9: Maximum Safe Operating Area

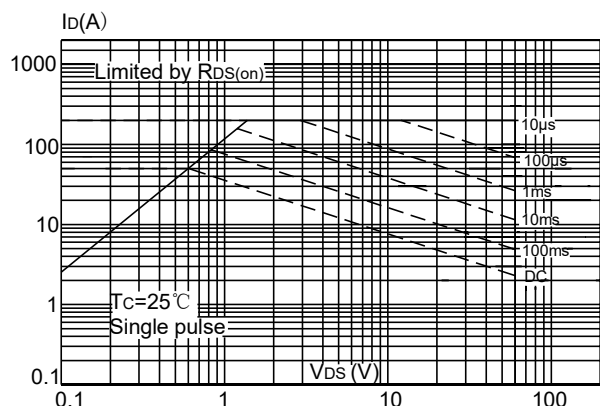


Figure 10: Maximum Continuous Drain Current vs. Case Temperature

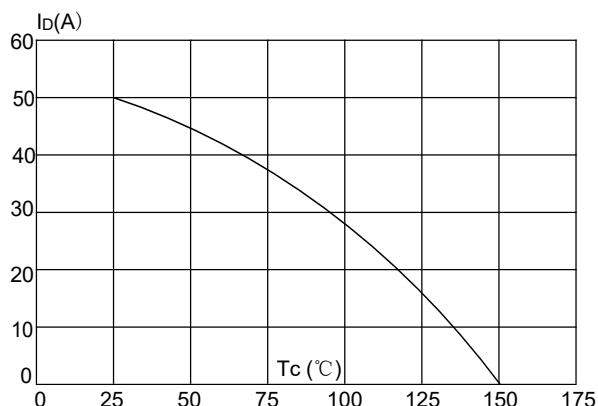
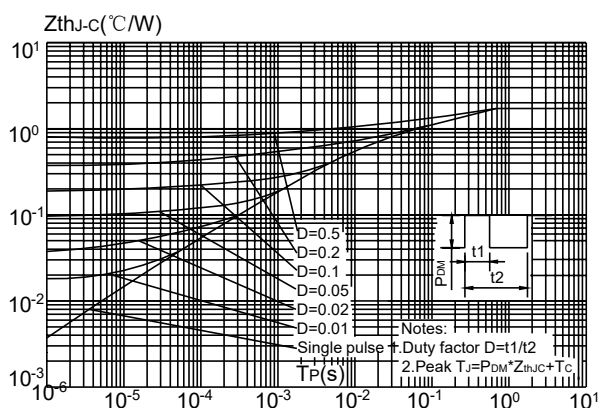
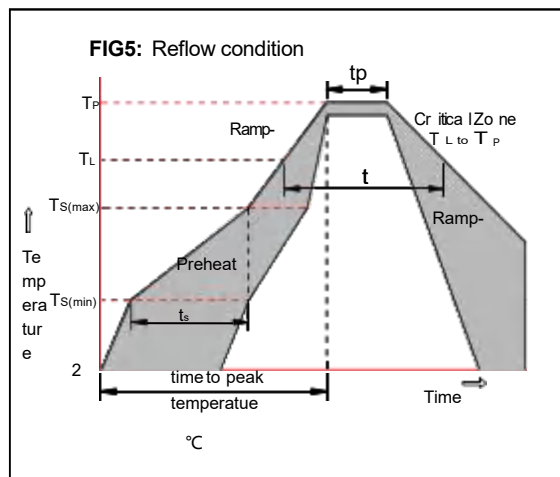


Figure.11: Maximum Effective Transient Thermal Impedance, Junction-to-Case



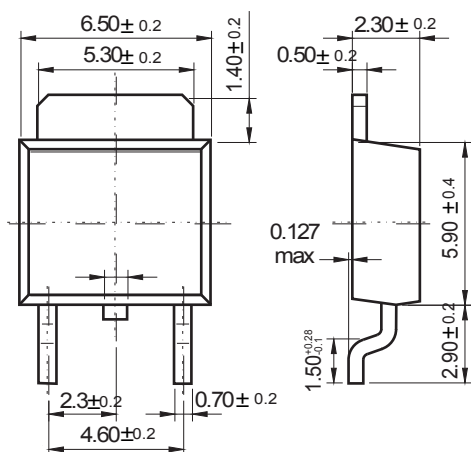
Soldering parameters

Reflow Condition		Pb-Free assembly (see as bellow)
Pre Heat	-Temperature Min ($T_{s(min)}$)	+150°C
	-Temperature Max($T_{s(max)}$)	+200°C
	-Time (Min to Max) (ts)	60-180 secs.
Average ramp up rate (Liquid us Temp (T_L) to peak)		3°C/sec. Max
$T_{s(max)}$ to T_L - Ramp-up Rate		3°C/sec. Max
Reflow	-Temperature(T_L)(Liquid us)	+217°C
	-Temperature(t_L)	60-150 secs.
Peak Temp (T_P)		+260(+0/-5)°C
Time within 5°C of actual Peak Temp (t_P)		30 secs. Max
Ramp-down Rate		6°C/sec. Max
Time 25°C to Peak Temp (T_P)		8 min. Max
Do not exceed		+260°C

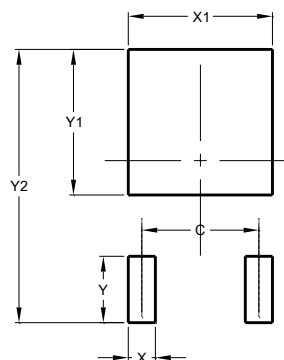


Package Dimensions & Suggested Pad Layout

TO-252

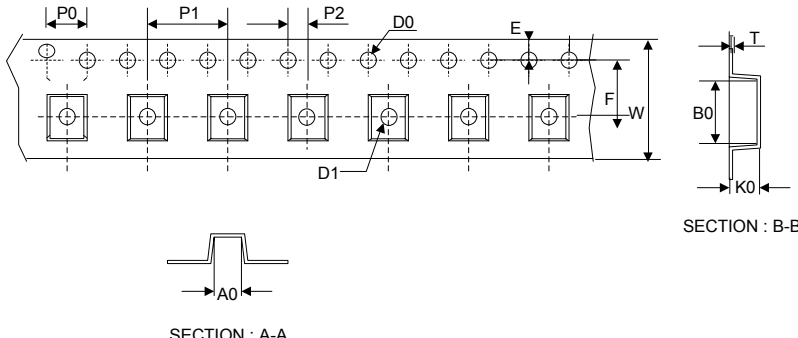
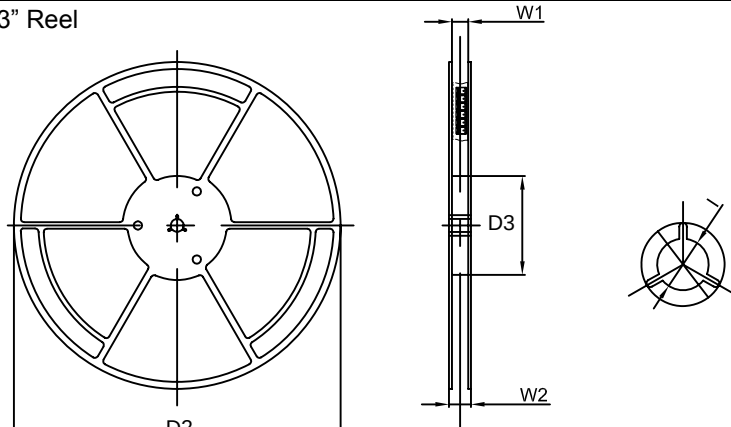


Dimensions in inches and (millimeters)



Dimensions	Value (in mm)
C	4.55
X	1.50
X1	5.80
Y	2.70
Y1	6.00
Y2	10.90

Tape & reel specification

Tape		Symbol	Dimension (mm)
 SECTION : A-A SECTION : B-B		P0	4.00±0.20
		P1	8.00±0.20
		P2	2.00±0.20
		D0	1.55±0.15
		D1	1.55±0.20
		E	1.75±0.20
		F	7.50±0.20
		W	16.00±0.20
		A0	7.10±0.20
		B0	10.50±0.20
		K0	2.70±0.20
		T	0.30±0.10
		D2	330.0±5.0
		D3	100.0±4.0
13" Reel		W1	20.0±5.0
		D2	330.0±5.0
		D3	100.0±4.0
		W1	20.0±5.0
		W2	25.0±5.0
		I	13.0±2.0
		Quantity: 2500PCS	